

# 74HC2G00; 74HCT2G00

Dual 2-input NAND gate

Rev. 04 — 3 July 2008

Product data sheet

## 1. General description

The 74HC2G00 and 74HCT2G00 are high-speed Si-gate CMOS devices. They provide two 2-input NAND gates.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

## 2. Features

- Wide supply voltage range from 2.0 V to 6.0 V
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
  - ◆ HBM JESD22-A114E exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$

## 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC2G00DP 74HCT2G00DP	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74HC2G00DC 74HCT2G00DC	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74HC2G00GD 74HCT2G00GD	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3 \times 2 \times 0.5$ mm	SOT996-2

## 4. Marking

Table 2. Marking code

Type number	Marking code
74HC2G00DP	H00
74HCT2G00DP	T00
74HC2G00DC	H00
74HCT2G00DC	T00
74HC2G00GD	H00
74HCT2G00GD	T00

## 5. Functional diagram

Fig 1. Logic symbol

Fig 2. IEC logic symbol

Fig 3. Logic diagram (one driver)

## 6. Pinning information

### 6.1 Pinning

Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)

Fig 5. Pin configuration SOT996-2 (XSON8U)

## 6.2 Pin description

**Table 3.** Pin description

Symbol	Pin	Description
1A, 2A	1, 5	data input
1B, 2B	2, 6	data input
GND	4	ground (0 V)
1Y, 2Y	7, 3	data output
V <sub>CC</sub>	8	supply voltage

## 7. Functional description

**Table 4.** Function table<sup>[1]</sup>

Input		Output
nA	nB	nY
L	L	H
L	H	H
H	L	H
H	H	L

[1] H = HIGH voltage level; L = LOW voltage level.

## 8. Limiting values

**Table 5.** Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	[1] -	±20	mA
I <sub>OK</sub>	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	[1] -	±20	mA
I <sub>O</sub>	output current	$V_O = -0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$	[1] -	25	mA
I <sub>CC</sub>	supply current		[1] -	50	mA
I <sub>GND</sub>	ground current		[1] -50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>D</sub>	dynamic power dissipation	T <sub>amb</sub> = -40 °C to +125 °C	[2] -	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K.  
 For VSSOP8 package: above 110 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K.  
 For XSON8 package: above 45 °C the value of P<sub>tot</sub> derates linearly with 2.4 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC2G00			74HCT2G00			Unit
			Min	Typ	Max	Min	Typ	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V <sub>I</sub>	input voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
V <sub>O</sub>	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 2.0 V	-	-	625	-	-	-	ns/V
		V <sub>CC</sub> = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V <sub>CC</sub> = 6.0 V	-	-	83	-	-	-	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T<sub>amb</sub> = 25 °C.

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
<b>74HC2G00</b>								
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	V
		V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	V
		V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 6.0 V	5.9	6.0	-	5.9	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 4.5 V	4.13	4.32	-	3.7	-	V
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>						
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V	-	0	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 4.5 V	-	0.15	0.33	-	0.4	V
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 6.0 V	-	-	±1.0	-	±1.0	μA
		I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	10	-	20	μA
I <sub>CC</sub>	supply current	per input pin; V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A; V <sub>CC</sub> = 6.0 V	-	-	10	-	20	μA
C <sub>I</sub>	input capacitance		-	1.5	-	-	-	pF

**Table 7. Static characteristics ...continued**

*Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .*

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
<b>74HCT2G00</b>								
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	2.0	1.6	-	2.0	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	1.2	0.8	-	0.8	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}\text{ or }V_{IL}$						
		$I_O = -20\text{ }\mu\text{A}; V_{CC} = 4.5\text{ V}$	4.4	4.5	-	4.4	-	V
		$I_O = -4.0\text{ mA}; V_{CC} = 4.5\text{ V}$	4.13	4.32	-	3.7	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}\text{ or }V_{IL}$						
		$I_O = 20\text{ }\mu\text{A}; V_{CC} = 4.5\text{ V}$	-	0	0.1	-	0.1	V
		$I_O = 4.0\text{ mA}; V_{CC} = 4.5\text{ V}$	-	0.15	0.33	-	0.4	V
$I_I$	input leakage current	$V_I = V_{CC}\text{ or GND}; V_{CC} = 5.5\text{ V}$	-	-	$\pm 1.0$	-	$\pm 1.0$	$\mu\text{A}$
$I_{CC}$	supply current	$V_I = V_{CC}\text{ or GND}; I_O = 0\text{ A}; V_{CC} = 5.5\text{ V}$	-	-	10	-	20	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	per input; $V_{CC} = 4.5\text{ V to }5.5\text{ V}; V_I = V_{CC} - 2.1\text{ V}; I_O = 0\text{ A}$	-	-	375	-	410	$\mu\text{A}$
$C_I$	input capacitance		-	1.5	-	-	-	pF

## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**

*Voltages are referenced to GND (ground = 0 V); all typical values are measured at  $T_{amb} = 25\text{ }^{\circ}\text{C}$ ; for test circuit see [Figure 7](#).*

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
<b>74HC2G00</b>								
$t_{pd}$	propagation delay	nA and nB to nY; see <a href="#">Figure 6</a> <a href="#">[1]</a>						
		$V_{CC} = 2.0\text{ V}$	-	25	95	-	110	ns
		$V_{CC} = 4.5\text{ V}$	-	9	19	-	22	ns
		$V_{CC} = 6.0\text{ V}$	-	7	16	-	20	ns
$t_t$	transition time	see <a href="#">Figure 6</a> <a href="#">[2]</a>						
		$V_{CC} = 2.0\text{ V}$	-	18	95	-	125	ns
		$V_{CC} = 4.5\text{ V}$	-	6	19	-	25	ns
		$V_{CC} = 6.0\text{ V}$	-	5	16	-	20	ns
$C_{PD}$	power dissipation capacitance	$V_I = \text{GND to }V_{CC}$ <a href="#">[3]</a>	-	10	-	-	-	pF

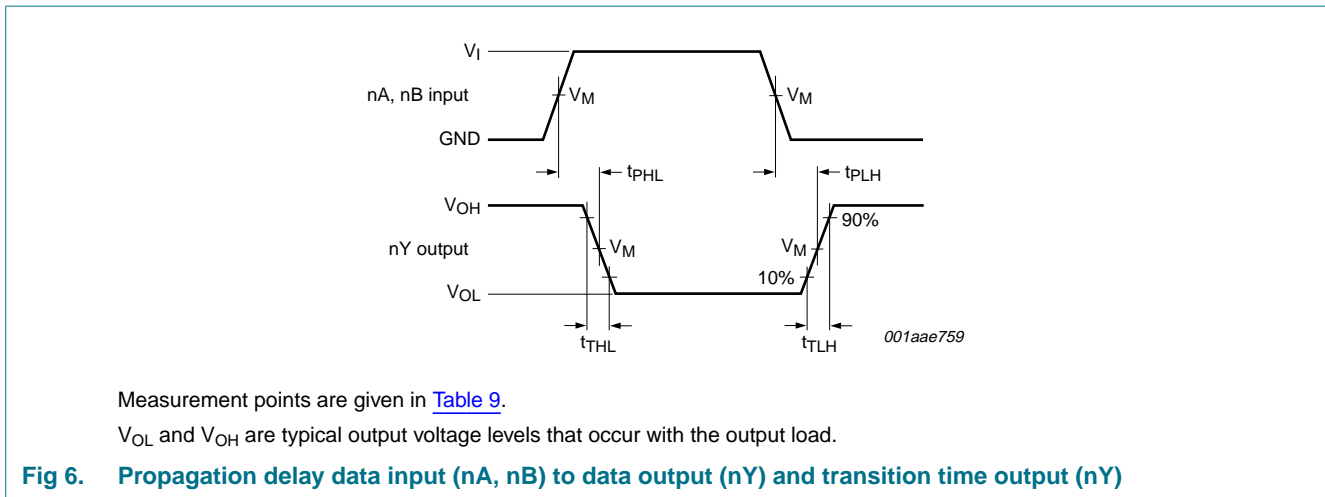
**Table 8. Dynamic characteristics ...continued**

Voltages are referenced to GND (ground = 0 V); all typical values are measured at  $T_{amb} = 25\text{ }^{\circ}\text{C}$ ; for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	-40 °C to +85 °C			-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
<b>74HCT2G00</b>								
$t_{pd}$	propagation delay	nA and nB to nY; see <a href="#">Figure 6</a>	[1]					
		$V_{CC} = 4.5\text{ V}$	-	12	24	-	29	ns
$t_t$	transition time	$V_{CC} = 4.5\text{ V}$ ; see <a href="#">Figure 6</a>	[2]	6	19	-	22	ns
$C_{PD}$	power dissipation capacitance	$V_I = \text{GND to } V_{CC} - 1.5\text{ V}$	[3]	10	-	-	-	pF

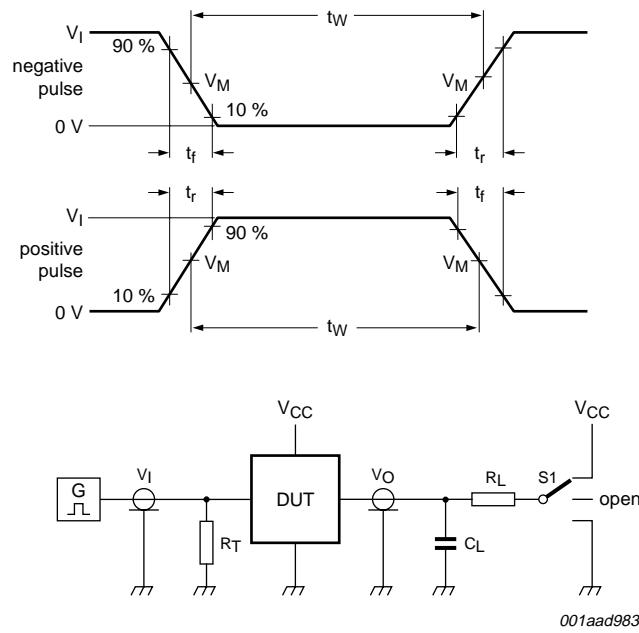
- [1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .
- [2]  $t_t$  is the same as  $t_{TLH}$  and  $t_{THL}$ .
- [3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu\text{W}$ ).  
 $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$  where:  
 $f_i$  = input frequency in MHz;  
 $f_o$  = output frequency in MHz;  
 $C_L$  = output load capacitance in pF;  
 $V_{CC}$  = supply voltage in V;  
 $N$  = number of inputs switching;  
 $\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

## 12. Waveforms



**Table 9. Measurement points**

Type	Input	Output
	$V_M$	$V_M$
74HC2G00	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74HCT2G00	1.3 V	1.3 V



Test data is given in [Table 10](#).

Definitions for test circuit:

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_L$  = Load resistance.

S1 = Test selection switch.

**Fig 7. Load circuit for measuring switching times**

**Table 10. Test data**

Type	Input		Load		S1 position
	$V_I$	$t_r, t_f$	$C_L$	$R_L$	$t_{PHL}, t_{PLH}$
74HC2G00	$V_{CC}$	$\leq 6$ ns	50 pF	1 k $\Omega$	open
74HCT2G00	3 V	$\leq 6$ ns	50 pF	1 k $\Omega$	open

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

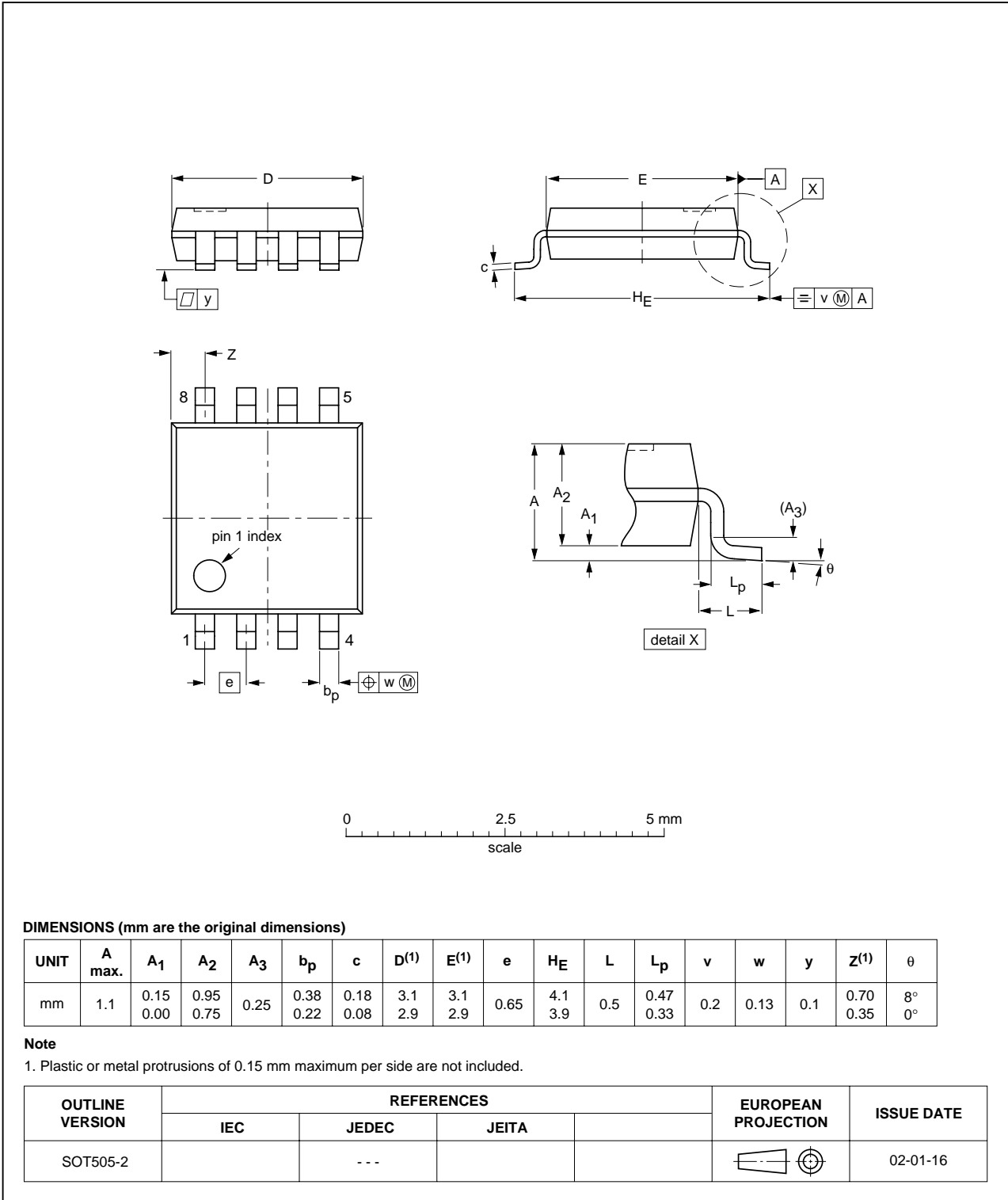


Fig 8. Package outline SOT505-2 (TSSOP8)



VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

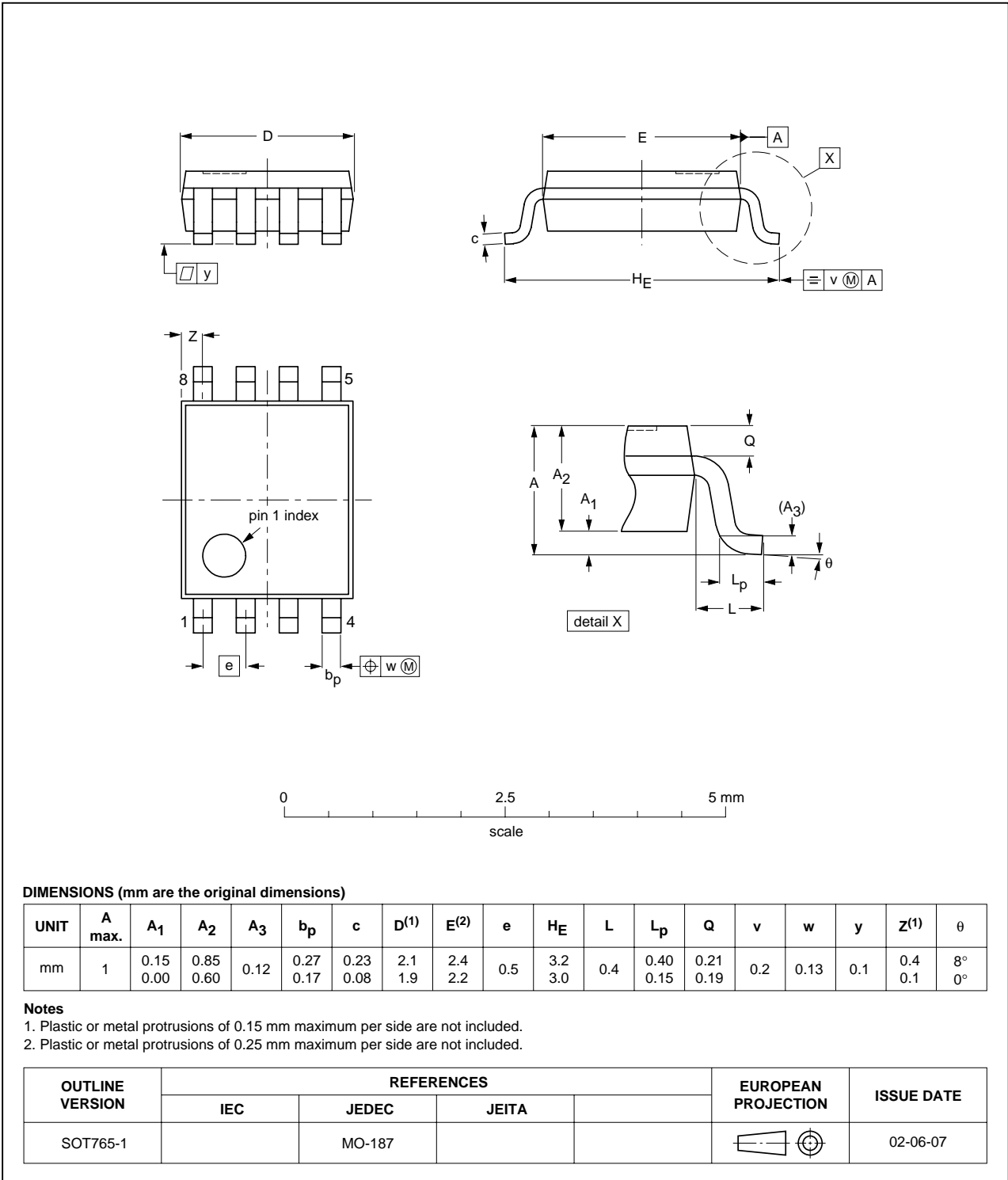


Fig 9. Package outline SOT765-1 (VSSOP8)

XSON8U: plastic extremely thin small outline package; no leads;  
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

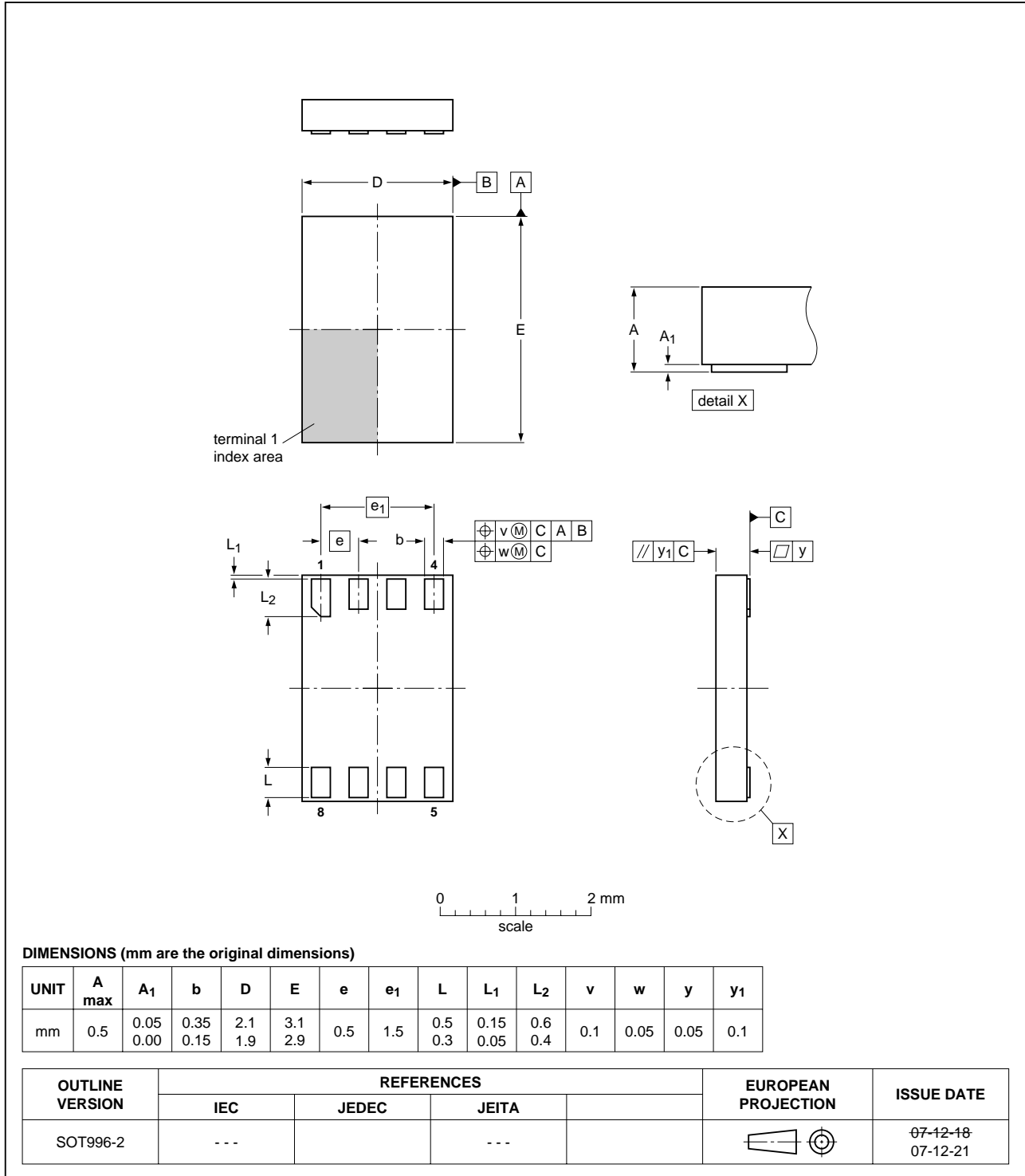


Fig 10. Package outline SOT996-2 (XSON8U)

## 14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT2G00_4	20080703	Product data sheet	-	74HC_HCT2G00_3
Modifications:		<ul style="list-style-type: none"> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Added type number 74HC2G00GD and 74HCT2G00GD (XSON8U package)</li> </ul>		
74HC_HCT2G00_3	20060405	Product data sheet	-	74HC_HCT2G00_2
74HC_HCT2G00_2	20030212	Product specification	-	74HC_HCT2G00_1
74HC_HCT2G00_1	20020710	Product specification	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

### 16.2 Definitions

**Draft** — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

**Short data sheet** — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

### 16.3 Disclaimers

**General** — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

**Right to make changes** — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

**Suitability for use** — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or

malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

**Applications** — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

**Limiting values** — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

**Terms and conditions of sale** — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

**No offer to sell or license** — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

### 16.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

## 17. Contact information

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

## 18. Contents

<b>1</b>	<b>General description</b> .....	<b>1</b>
<b>2</b>	<b>Features</b> .....	<b>1</b>
<b>3</b>	<b>Ordering information</b> .....	<b>1</b>
<b>4</b>	<b>Marking</b> .....	<b>2</b>
<b>5</b>	<b>Functional diagram</b> .....	<b>2</b>
<b>6</b>	<b>Pinning information</b> .....	<b>2</b>
6.1	Pinning .....	2
6.2	Pin description .....	3
<b>7</b>	<b>Functional description</b> .....	<b>3</b>
<b>8</b>	<b>Limiting values</b> .....	<b>3</b>
<b>9</b>	<b>Recommended operating conditions</b> .....	<b>4</b>
<b>10</b>	<b>Static characteristics</b> .....	<b>4</b>
<b>11</b>	<b>Dynamic characteristics</b> .....	<b>5</b>
<b>12</b>	<b>Waveforms</b> .....	<b>6</b>
<b>13</b>	<b>Package outline</b> .....	<b>8</b>
<b>14</b>	<b>Abbreviations</b> .....	<b>11</b>
<b>15</b>	<b>Revision history</b> .....	<b>11</b>
<b>16</b>	<b>Legal information</b> .....	<b>12</b>
16.1	Data sheet status .....	12
16.2	Definitions .....	12
16.3	Disclaimers .....	12
16.4	Trademarks .....	12
<b>17</b>	<b>Contact information</b> .....	<b>12</b>
<b>18</b>	<b>Contents</b> .....	<b>13</b>

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.



© NXP B.V. 2008.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: [salesaddresses@nxp.com](mailto:salesaddresses@nxp.com)

Date of release: 3 July 2008

Document identifier: 74HC\_HCT2G00\_4